

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

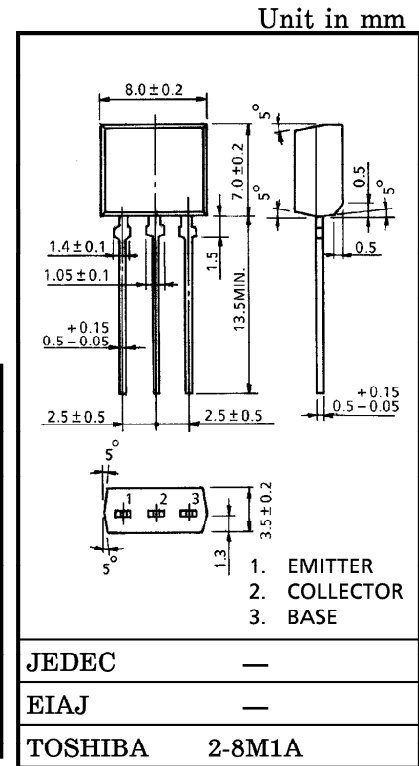
2SB1602

POWER AMPLIFIER APPLICATIONS

- High DC Current Gain
: $h_{FE(1)} = 300 \sim 1000$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.5V$ (Typ.)
- Complementary to 2SD2462

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current	DC	I_C	-3
	Pulse	I_{CP}	-6
Base Current	I_B	-0.6	A
Collector Power Dissipation	P_C	1.3	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



Weight : 0.55g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -60V, I_E = 0$	—	—	-100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -7V, I_C = 0$	—	—	-100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-60	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -5V, I_C = -0.5A$	300	—	1000	
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -1.5A$	350	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -20mA$	—	-0.5	-1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -0.5A$	—	-0.7	-1.0	V
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	60	—	pF

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